

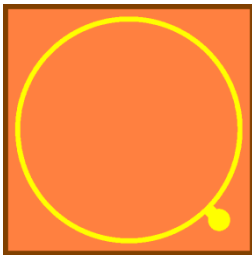
# GCS large Area InGaAs Monitor PIN PD

P/N: Do237\_1.5mm\_P2



Known Good Die

## PRELIMINARY DATASHEET



### Introduction

This product is a front side illuminated InGaAs large area monitor PIN photodiode chip that features a planar structure with anode on front side and cathode on backside. This product has a large 1.5mm detection window, with an excellent responsivity in the wavelength region from 980nm to 1620nm, mainly designed for various LD monitoring application.

### Key Features

- Planar structure on n+ InP substrate with top anode contact
- 1.5mm optical detection window optimized for LD monitoring
- Low operating bias voltage
- -40C to 85C operation range
- Deliverable in GCS Known Good Die™ with 100% testing and inspection
- RoHS compliant
- Customized chip dimension available

### Applications

- Large area LD monitoring

### SPECIFICATIONS (T=25C°)

	Conditions	Min.	Typical	Max.	Unit	Notes
Responsivity	1310nm	0.8	0.9	-	A/W	
	1550nm	0.9	0.95	-	A/W	
Capacitance	-5 V	-	75	-	pF	
Breakdown	1μA	20	-	-	V	
Dark current	-5V	-	1.0	2.5	nA	

### ABSOLUTE MAXIMUM RATING

Parameter	Rating
Reverse Voltage	-20V
Reverse Current	-10mA
Forward Current	10mA
Optical Power Input	10mW
Operating Temperature	-40C to 85C
Storage Temperature	-55C to 125C
Soldering Temperature	320C / 5 sec

### Global Communication Semiconductors, LLC

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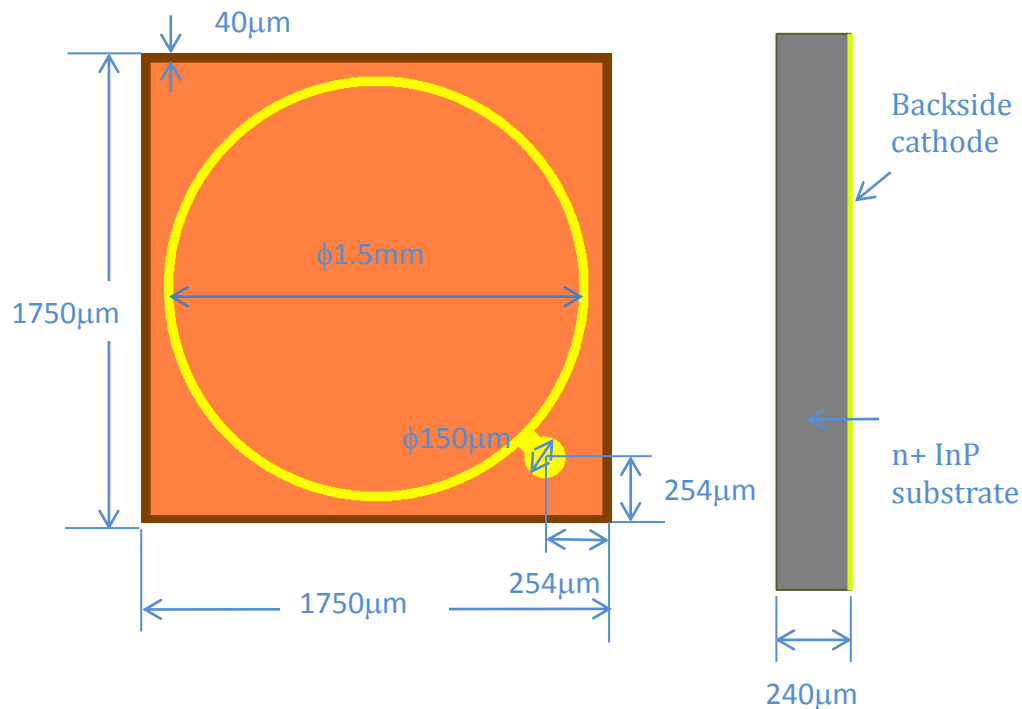
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## DIMENSIONS

Made in USA

	Conditions	Min.	Typical	Max.	Unit	Notes
Detection Window			1500		μm	
Bonding pad diameter			150		μm	for p-pad
Metal height of bond pads			1.6	-	μm	Au metal
Die height		230	240	250	μm	
Die width		1740	1750	1760	μm	
Die length		1740	1750	1760	μm	



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Attention: InP brittle material and electrostatic sensitive device, observe precaution for handling.

## About GCS:

GCS has a long history manufacturing and shipping both GaAs and InGaAs based photo diodes since 2000. Our state of art manufacturing facility is located in Torrance, California, and has about 10,000 square feet of fab space with a capability of about 1200 4-inch wafers per month and expandable to 2000 wafers per month. GCS as a world-class semiconductor device manufacturer has been delivering a total of over 30 million photo diodes with various data rates and applications used for optical communications, which have been deployed in field by top tier optical transceiver companies worldwide. ■

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